



ABSTRACT OF THE DISCLOSURE

~~The present invention provides a step in which a A channel-length of a TFT can~~
be controlled with higher reproducibility. ~~In addition, the present invention provides a~~
~~step in which reproducibility, and~~ a short channel-length of the TFT can be
manufactured. Further, ~~the present invention provides a structure of the TFT in which a~~
having an improved current-voltage characteristic ~~can be improved~~ is provided. The
~~present invention refers to a A thin film transistor comprising~~ has a lamination layer
~~wherein~~ where a first conductive film, a first insulating film and a second conductive film
are sequentially laminated, a semiconductor film is formed so as to be in contact with
the side surface of the lamination layer, and a third conductive film ~~covering~~ covers the
semiconductor film through a second insulating film. The first conductive film and the
second conductive film are a source electrode and a drain electrode, ~~[[and]]~~ a region
which is in contact with the first insulating film and the third conductive film is a channel
forming region in the semiconductor film, and the third conductive film is a gate
electrode.